



## TO-92MOD Plastic-Encapsulated Transistors

### 2SC2060 TRANSISTOR (NPN)

#### FEATURE

Power dissipation

$$P_{CM}: 0.75 \text{ W (Tamb=25°C)}$$

Collector current

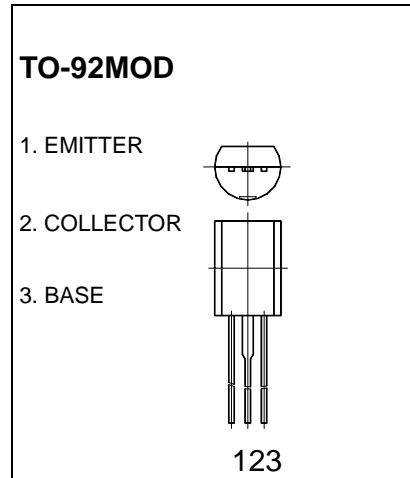
$$I_{CM}: 1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	32		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 40V, I_E = 0$		0.5	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$		0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = 3V, I_C = 100mA$	80	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.4	V